

Author Index of Volume A28

- | | | | |
|-------------------------|-------------------------|----------------------------|-------------------------------|
| Afanas'ev, V. V., 197 | Grigoriev, S. A., 179 | Mochalkina, O. R., 173 | Singh, V. R., 7 |
| Agrawal, R., 21 | Guckel, H., 133 | Mogilevski, A. N., 35 | Smits, J. G., 41 |
| Artyomav, V. M., 223 | Gumenjuk, S. V., 231 | Mosser, V., 113 | Spasov, L., 35 |
| Audet, S. A., 13 | Gurova, I. N., 179 | Mukhametshin, R. G., 173 | Srivastava, S. K., 21 |
| Berezkin, V. A., 191 | Harris, P. R., 147 | Naito, Y., 63 | Stavrovski, D. B., 35 |
| Bobrov, P. V., 197 | Inkin, V. N., 191 | Novikov, V. N., 179 | Stroganova, N. S., 35 |
| Bocharov, Yu. V., 179 | Kanda, Y., 83 | Obermeier, E., 113 | Stuchebnikov, V. M., 207 |
| Borisenko, A. Yu., 173 | Kapustina, O. A., 179 | Odintsov, M. A., 203 | Sushentsov, N. I., 203 |
| Buser, R. A., 71 | Kartashev, A. S., 197 | Panagou, J. G., 147 | Suski, J., 113 |
| Chau, K. H.-L., 147 | Kodama, S., 63 | Podlepetsky, B. I., 231 | Suzhi Wu, 1 |
| Cooney, T. K., 41 | Kodato, S., 63 | Polyanskykh, N. A., 231 | Tarantov, Yu. A., 197 |
| Dalke, S. I., 41 | Kremliov, V. V., 231 | Prasad, A., 7 | Vaganov, V. I., 159, 161, 215 |
| Demianovich, M. V., 179 | Kruchinin, A. A., 197 | Prjakhin, G. D., 215 | Vikulin, I. M., 185 |
| de Rooij, N. F., 71 | Kudryashov, E. A., 223 | Qinggui Chen, 153 | Vlasov, Yu. G., 197 |
| Dwivedi, R., 21 | Kudryavtzev, T. L., 203 | Qiu Anping, 29 | Weiyan Wang, 153 |
| Frank, R., 93 | Kuroda, K., 63 | Remizova, E. I., 179 | Xinyu Zheng, 1 |
| Fung, C. D., 147 | Lianzhong Yu., 105 | Reshetov, V. N., 179 | Yadava, P. K., 21 |
| Galkina, I. P., 35 | Limanov, A. B., 215 | Rychkov, G. S., 191 | Yan Wang, 105 |
| Givargizov, E. I., 215 | Mayorov, A. D., 35 | Schooneveld, E. M., 13 | Yegorov, V. V., 185 |
| Glauberger, M. A., 185 | Middelhoek, S., 13 | Shelenshkevich, V. A., 223 | Yuan Libo, 29 |
| Goss, J., 113 | Mihailov, D., 35 | Shulga, A. I., 223 | Zaharieva, R., 35 |
| Grabchak, V. P., 191 | Minhang Bao, 81, 105 | | |

Subject Index of Volume A28

- Acoustic power measurement
 - effect of ultrasonic stress on sensitivity of Si strain devices and application to, 7
- Aluminium nitride films
 - for SAW sensors, 203
- Anisotropic etching
 - ASEP: CAD program for Si, 71
- Arsenic
 - hydrogen concentration GaAs detectors, 191
- ASEP
 - CAD program for Si anisotropic etching, 71
- Automatic intensity compensation
 - fiber-optic diaphragm pressure sensor with, 29
- CAD program
 - for Si anisotropic etching; ASEP, 71
- Construction problems
 - in sensors, 161
- Current output mode
 - of MOS magnetic field sensor, general characteristics and, 1
- Fiber-optic diaphragm
 - pressure sensor with automatic intensity compensation, 29
- Force transducers
 - SOS strain gauge sensors for, 207
- Frequency output
 - integrated magnetic field sensor with, 231
- Gallium
 - hydrogen concentration GaAs detectors, 191
- Germanium
 - high-accuracy, quick-response optical power sensor with $\mu\text{c-Ge:H}$ thin film, 63
- Hydrogen concentration
 - GaAs detectors, 191
- Impurity profile
 - analysis of n-channel MOSFET magnetic sensor with non-uniform, 21
- Injection-inversion magnetosensitive structure, 185
- ISFET
 - optical and thermal sensitivity of pH-ISFET with Ta_2O_5 membrane, 197
- Laser beam focusing
 - hardware and software complex for automatic, and adjustment based on circular-radial phototransistor array, 173
- Liquid crystal sensors
 - of physical signals, 179
- Magnetic field sensor
 - general characteristics and current output mode of MOS, 1
 - integrated, with frequency output, 231
- Magnetic sensor
 - analysis of n-channel MOSFET, with non-uniform impurity profile, 21
- Magnetosensitive structure
 - injection-inversion, 185
- Mercury vapour
 - measurement of concentration of, in air through piezoresonance method, 35
- Microelectronics
 - pressure sensors merge micromachining and, 93
- Micromachining
 - pressure sensors merge, and microelectronics, 93
- Modulation depth
 - Si capacitive pressure transducer with increased, 223
- MOS
 - magnetic field sensor, general characteristics and current output mode of, 1
- MOSFET
 - magnetic sensor with non-uniform impurity profile, analysis of n-channel, 21
- Optical power sensor
 - high-accuracy quick-response, with $\mu\text{c-Ge:H}$ thin film, 63
- Optical sensitivity
 - of pH-ISFET with Ta_2O_5 membrane, 197
- pH-ISFET
 - optical and thermal sensitivity of, with Ta_2O_5 membrane, 197
- Phototransistor array
 - hardware and software complex for automatic laser beam focusing and adjustment based on, 173
- Physical signals
 - liquid crystal sensors of, 179
- Piezoelectric bimorphs
 - constituent equations of, 41
- Piezoresistance effect
 - of Si, 83
- Piezoresistive pressure sensors
 - based on polycrystalline Si, 113
- Piezoresonance method
 - measurement of concentration of Hg vapour in air through, 35
- Pressure sensor(s)
 - epitaxial Si on zirconia (SOZ), 153
 - fiber-optic diaphragm, with automatic intensity compensation, 29
 - merge micromachining and microelectronics, 93
 - over-range behaviour of sealed-cavity polysilicon, 147
 - piezoresistive, based on polycrystalline Si, 113
 - silicon-on-insulator (SOI) structures for, 215
 - stress concentration structure with front beam for, 105
- Pressure transducer(s)
 - Si capacitive, with increased modulation depth, 223

- SOS strain gauge sensors for force and, 207
 - surface micromachined, 133
- Sensor array
 - high-purity Si, for imaging soft X-ray radiation, 13
- SAW sensors
 - AlN films for, 203
- Silicon
 - ASEP: CAD program for Si anisotropic etching, 71
 - capacitive pressure transducer with increased modulation depth, 223
 - effect of ultrasonic stress on sensitivity of Si strain devices and application to acoustic power measurement, 7
 - epitaxial Si on zirconia (SOZ) pressure sensor, 153
 - high-purity Si sensor array for imaging soft X-ray radiation, 13
 - over-range behaviour of sealed-cavity polysilicon pressure sensors, 147
 - piezoresistance effect of Si, 83
 - piezoresistive pressure sensors based on polycrystalline Si, 113
 - SOI structures for pressure sensors, 215
- SOI
 - silicon-on-insulator (SOI) structures for pressure sensors, 215
- SOS
 - strain gauge sensors for force and pressure transducers, 207
- Strain devices
 - effect of ultrasonic stress on sensitivity of Si, and application to acoustic power measurement, 7
- Strain gauge sensors
 - SOS, for force and pressure transducers, 207
- Stress concentration structure
 - with front beam for pressure sensor, 105
- Tantalum
 - optical and thermal sensitivity of pH-ISFET with Ta₂O₅ membrane, 197
- Thermal sensitivity
 - of pH-ISFET with Ta₂O₅ membrane, 197
- Ultrasonic stress
 - effect of, on sensitivity of Si strain devices and application to acoustic power measurement, 7
- X-ray radiation
 - high-purity Si sensor array for imaging, 13
- Zirconia
 - epitaxial Si on zirconia (SOZ) pressure sensor, 153

